PD - 9.1123

International IOR Rectifier

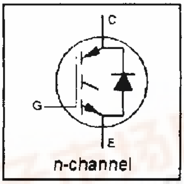
IRGPC50KD2

INSULATED GATE BIPOLAR TRANSISTOR WITH ULTRAFAST SOFT RECOVERY DIODE

Short Circuit Rated UltraFast CoPack IGBT

Features

- Short circuit rated -10µs @125°C, V_{GE} = 15V
- Switching-loss rating includes all "tail" losses
- HEXFRED™ soft ultrafast diodes
- Optimized for high operating frequency (over 5kHz)



V_{CES} = 600V

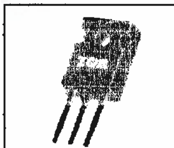
$V_{CE(sat)}$ ≤ 2.7V

@V_{GE} = 15V, I_C = 30A

Description

Co-packaged IGBTs are a natural extension of International Rectifier's well known IGBT line. They provide the convenience of an IGBT and an ultrafast recovery diode in one package, resulting in substantial benefits to a host of high-voltage, high-current, applications.

These new short circuit rated devices are especially suited for motor control and other applications requiring short circuit withstand capability.



TO-247AC

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Voltage	600	V
I_C @ T_C = 25°C	Continuous Collector Current	52	A
I_C @ T_C = 100°C	Continuous Collector Current	30	
I_{CM}	Pulsed Collector Current ①	100	
I_{LM}	Clamped Inductive Load Current ②	100	
I_F @ T_C = 100°C	Diode Continuous Foward Current	25	
I_{FM}	Diode Maximum Forward Current	100	
t_{sc}	Short Circuit Withstand Time	10	µs
V_{GE}	Gate-to-Emitter Voltage	± 20	V
P_D @ T_C = 25°C	Maximum Power Dissipation	200	W
P_D @ T_C = 100°C	Maximum Power Dissipation	52	
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to +150	°C
	Soldering Temperature, for 10 sec.	300 (0.063 in. (1.6mm) from case)	
	Mounting Torque, 6-32 or M3 Screw.	10 lbf•in (1.1 N•m)	

Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case - IGBT	-----	-----	0.64	°C/W
$R_{\theta JC}$	Junction-to-Case - Diode	-----	-----	0.83	
$R_{\theta CS}$	Case to Sink, flat, greased surface	-----	0.24	-----	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount	-----	-----	40	
Wt	Weight	-----	6 (0.21)	-----	g (oz)

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Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage ③	600	----	----	V	V_{GE} = 0V, I_C = 250μA
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	----	0.60	----	V/°C	V_{GE} = 0V, I_C = 1.0mA
$V_{CE(on)}$	Collector-to-Emitter Saturation Voltage	----	2.0	2.7	V	I_C = 30A, V_{GE} = 15V
		----	2.6	----		I_C = 52A, V_{GE} = 15V
		----	2.3	----		I_C = 30A, T_J = 150°C, V_{GE} = 15V
$V_{GE(th)}$	Gate Threshold Voltage	3.0	----	5.5		V_{CE} = V_{GE}, I_C = 250μA
$\Delta V_{GE(th)}/\Delta T_J$	Temperature Coeff. of Threshold Voltage	----	-14	----	mV/°C	V_{CE} = V_{GE}, I_C = 250μA
g_{fe}	Forward Transconductance ④	9.8	17	----	S	V_{CE} = 100V, I_C = 30A
I_{CES}	Zero Gate Voltage Collector Current	----	----	250	μA	V_{GE} = 0V, V_{CE} = 600V
		----	----	6500		V_{GE} = 0V, V_{CE} = 600V, T_J = 150°C
V_{FM}	Diode Forward Voltage Drop	----	1.3	1.7	V	I_C = 25A
		----	1.2	1.5		I_C = 25A, T_J = 150°C
I_{GES}	Gate-to-Emitter Leakage Current	----	----	±100	nA	V_{GE} = ±20V

Switching Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q_g	Total Gate Charge (turn-on)	----	120	200	nC	I_C = 30A
Q_{ge}	Gate - Emitter Charge (turn-on)	----	27	42		V_{CC} = 400V
Q_{gc}	Gate - Collector Charge (turn-on)	----	44	73		
$t_{d(on)}$	Turn-On Delay Time	----	74	----	ns	T_J = 25°C
t_r	Rise Time	----	100	----		I_C = 30A, V_{CC} = 480V
$t_{d(off)}$	Turn-Off Delay Time	----	260	460		V_{GE} = 15V, R_G = 5.0Ω
t_f	Fall Time	----	190	290		Energy losses include "tail" and
E_{on}	Turn-On Switching Loss	----	2.1	----	mJ	diode reverse recovery
E_{off}	Turn-Off Switching Loss	----	0.9	----		
E_{ts}	Total Switching Loss	----	3.0	4.5		
t_{sc}	Short Circuit Withstand Time	10	----	----	μs	V_{CC} = 360V, T_J = 125°C V_{GE} = 15V, R_G = 5.0Ω, V_{CPK} < 500V
$t_{d(on)}$	Turn-On Delay Time	----	77	----	ns	T_J = 150°C
t_r	Rise Time	----	100	----		I_C = 30A, V_{CC} = 480V
$t_{d(off)}$	Turn-Off Delay Time	----	530	----		V_{GE} = 15V, R_G = 5.0Ω
t_f	Fall Time	----	360	----		Energy losses include "tail" and
E_{ts}	Total Switching Loss	----	4.5	----	mJ	diode reverse recovery
L_E	Internal Emitter Inductance	----	13	----	nH	Measured 5mm from package
C_{ies}	Input Capacitance	----	2900	----	pF	V_{GE} = 0V
C_{oes}	Output Capacitance	----	220	----		V_{CC} = 30V
C_{res}	Reverse Transfer Capacitance	----	30	----		f = 1.0MHz
t_{rr}	Diode Reverse Recovery Time	----	50	75	ns	T_J = 25°C; I_F = 25A, V_R = 200V, di/dt = 200A/μs
		----	105	160		T_J = 125°C
I_{rr}	Diode Peak Reverse Recovery Current	----	4.5	10	A	T_J = 25°C
		----	8.0	15		T_J = 125°C
Q_{rr}	Diode Reverse Recovery Charge	----	112	375	nC	T_J = 25°C
		----	420	1200		T_J = 125°C
$di_{(rec)M}/dt$	Diode Peak Rate of Fall of Recovery During t_b	----	250	----	A/μs	T_J = 25°C
		----	160	----		T_J = 125°C

Notes:

① Repetitive rating; V_{GE}=20V, pulse width limited by max. junction temperature

② V_{CC}=80%(V_{CES}), V_{GE}=20V, L=10μH, R_G= 5.0Ω

③ Pulse width ≤ 80μs, duty factor ≤ 0.1%.

④ Pulse width 5.0μs, single shot.

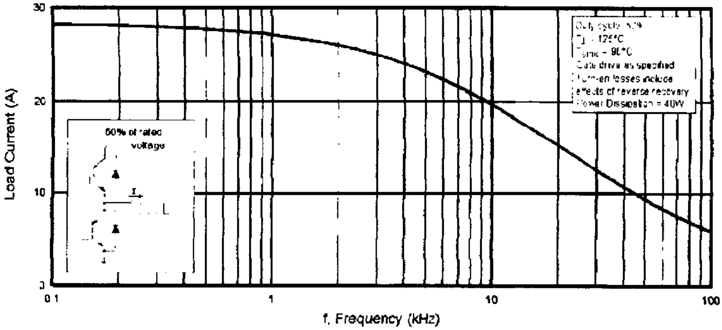

Fig. 1 - Typical Load Current vs. Frequency
(Load Current = I_{RMS} of fundamental)

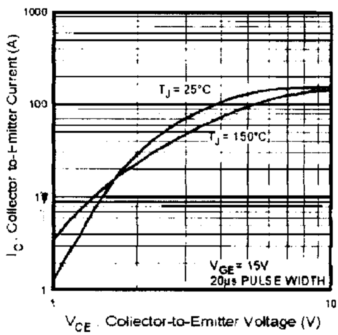

Fig. 2 - Typical Output Characteristics

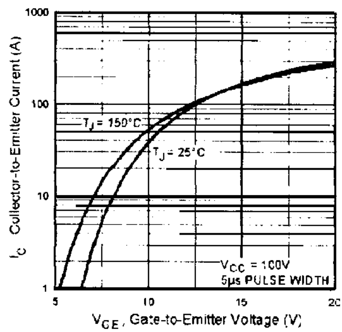

Fig. 3 - Typical Transfer Characteristics

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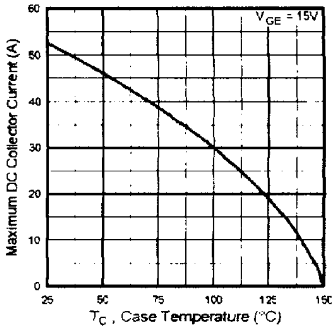

Fig. 4 - Maximum Collector Current vs. Case Temperature

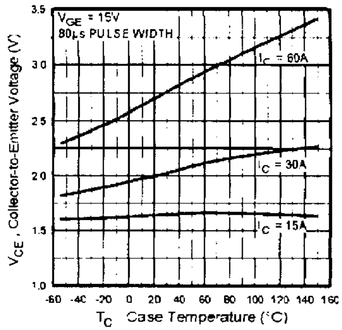

Fig. 5 - Collector-to-Emitter Voltage vs. Case Temperature

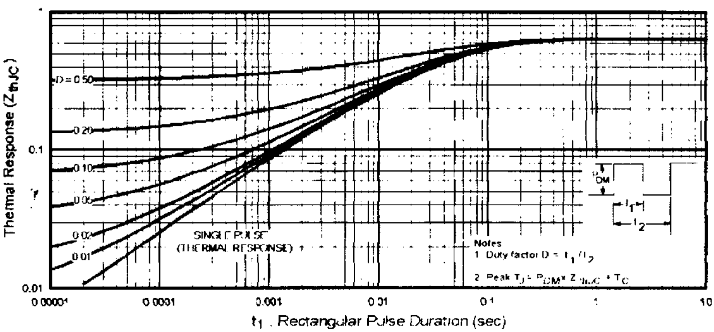

Fig. 6 - Maximum IGBT Effective Transient Thermal Impedance, Junction-to-Case

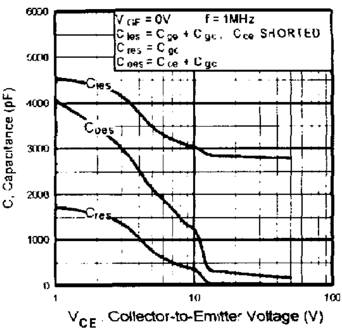

Fig. 7 - Typical Capacitance vs. *Collector-to-Emitter Voltage*

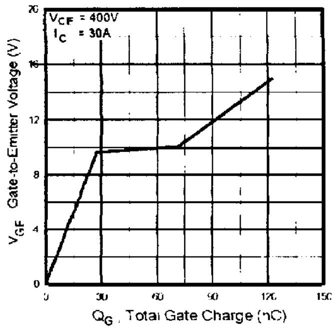

Fig. 8 - Typical Gate Charge vs Gate-to-Emitter Voltage

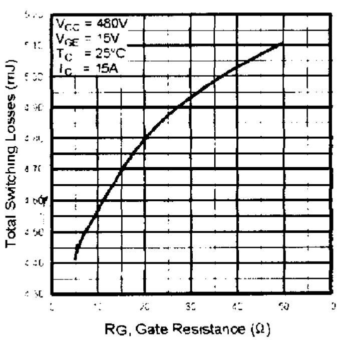

Fig. 9 - Typical Switching Losses vs Gate Resistance

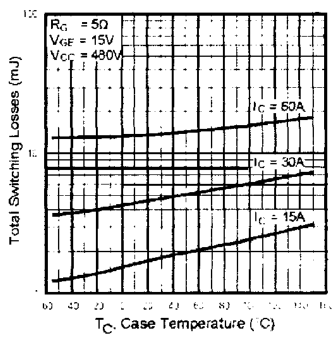

Fig. 10 - Typical Switching Losses vs Case Temperature

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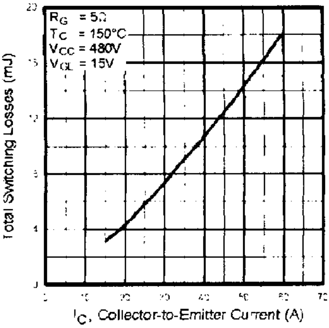

Fig. 11 - Typical Switching Losses vs. Collector-to-Emitter Current

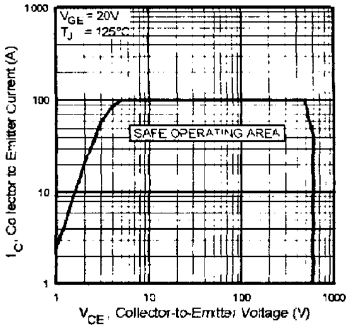

Fig. 12 - Turn-Off SOA

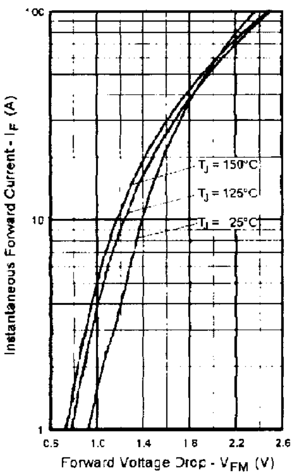

Fig. 13 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

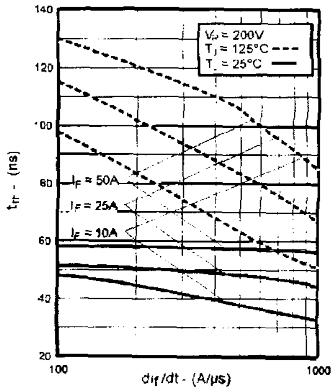

Fig. 14 - Typical Reverse Recovery vs di_f/dt

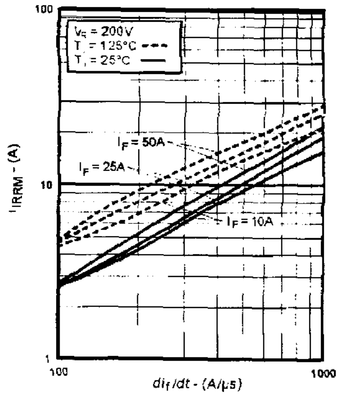

Fig. 15 - Typical Recovery Current vs di_f/dt

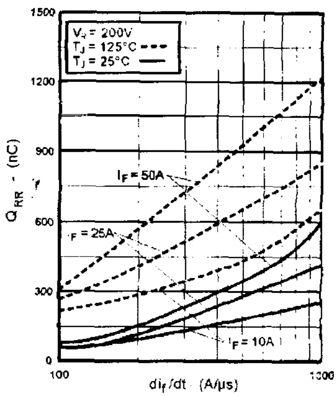

Fig. 16 - Typical Stored Charge vs di_f/dt

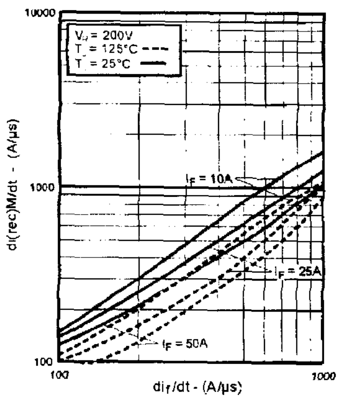

Fig. 17 - Typical $di_{(rec)M}/dt$ vs di_f/dt

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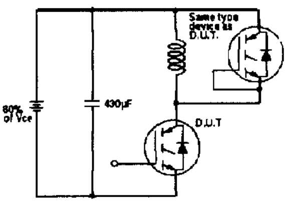

Fig. 18a - Test Circuit for Measurement of I_{LM}, E_{on}, $E_{off(diode)}$, t_{rr}, Q_{rr}, I_{rr}, $t_{d(on)}$, t_r, $t_{d(off)}$, t_f

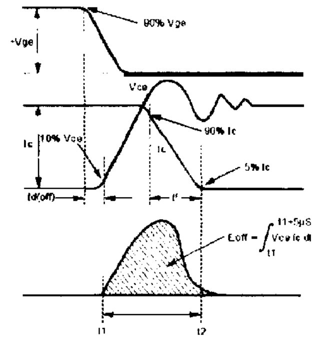

Fig. 18b - Test Waveforms for Circuit of Fig. 18a, Defining E_{off}, $t_{d(off)}$, t_f

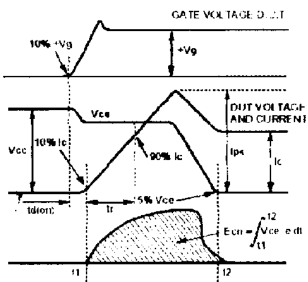

Fig. 18c - Test Waveforms for Circuit of Fig. 18a, Defining E_{on}, $t_{d(on)}$, t_r

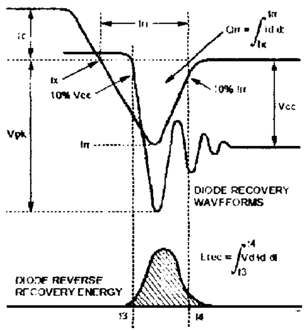

Fig. 18d - Test Waveforms for Circuit of Fig. 18a, Defining E_{rec}, t_{rr}, Q_{rr}, I_{rr}

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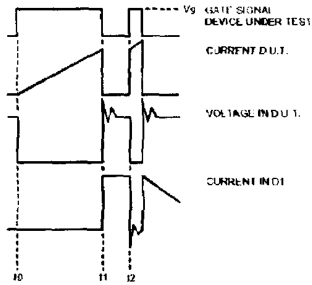


Fig. 18e - Macro Waveforms for Test Circuit of Fig. 18a

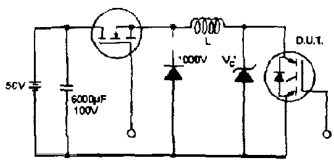


Fig. 19 - Clamped Inductive Load Test Circuit

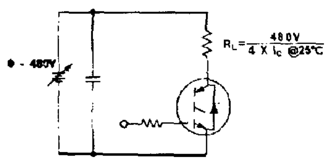
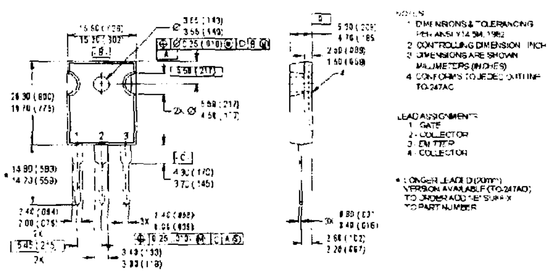


Fig. 20 - Pulsed Collector Current Test Circuit



CONFORMS TO JEDEC OUTLINE TO-247AC (TO-3P)
Dimensions in Millimeters and (Inches)